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Microsemi
POWER PRODUCTS GROUP

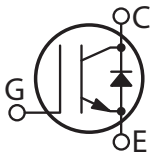
APT75GT120JRDQ3

1200V

Thunderbolt IGBT®

The Thunderblot IGBT® is a new generation of high voltage power IGBTs. Using Non- Punch Through Technology, the Thunderblot IGBT® offers superior ruggedness and ultrafast switching speed.

- Low Forward Voltage Drop
- High Freq. Switching to 20KHz
- Low Tail Current
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated



MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT75GT120JRDQ3	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	±30	
I_{C1}	Continuous Collector Current @ T_C = 25°C	97	Amps
I_{C2}	Continuous Collector Current @ T_C = 110°C	42	
I_{CM}	Pulsed Collector Current [1] @ T_C = 150°C	225	
SSOA	Switching Safe Operating Area @ T_J = 150°C	225	
P_D	Total Power Dissipation	480	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 4mA)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 3mA, T_j = 25°C)	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 75A, T_j = 25°C)	2.7	3.2	3.7	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 75A, T_j = 125°C)		3.9		
I_{CES}	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 25°C) [2]			200	µA
	Collector Cut-off Current (V_{CE} = 1200V, V_{GE} = 0V, T_j = 125°C) [2]			2000	
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V)			480	nA
$R_{G(int)}$	Intergrated Gate Resistor		5		Ω

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance		5100		pF
C_{oes}	Output Capacitance	V_{GE} = 0V, V_{CE} = 25V		720		
C_{res}	Reverse Transfer Capacitance	f = 1 MHz		380		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge		10		V
Q_g	Total Gate Charge [3]	V_{GE} = 15V		500		nC
Q_{ge}	Gate-Emitter Charge	V_{CE} = 600V		32		
Q_{gc}	Gate-Collector ("Miller") Charge	I_C = 75A		516		
SSOA	Switching Safe Operating Area	T_J = 150°C, R_G = 4.3Ω, V_{GE} = 15V, L = 100µH,V_{CE} = 1200V	225			A
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		50		ns
t_r	Current Rise Time	V_{CC} = 800V		65		
$t_{d(off)}$	Turn-off Delay Time	V_{GE} = 15V		375		
t_f	Current Fall Time	I_C = 75A		25		
E_{on1}	Turn-on Switching Energy [4]	R_G = 1.0Ω		8045		µJ
E_{on2}	Turn-on Switching Energy (Diode) [5]	T_J = +25°C		8845		
E_{off}	Turn-off Switching Energy [6]			2970		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		50		ns
t_r	Current Rise Time	V_{CC} = 800V		65		
$t_{d(off)}$	Turn-off Delay Time	V_{GE} = 15V		415		
t_f	Current Fall Time	I_C = 75A		29		
E_{on1}	Turn-on Switching Energy [4]	R_G = 1.0Ω		8050		µJ
E_{on2}	Turn-on Switching Energy (Diode) [5]	T_J = +125°C		12660		
E_{off}	Turn-off Switching Energy [6]			4215		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.26	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			.56	
W_T	Package Weight		29.2		gm
$V_{Isolation}$	RMS Voltage (50-60hHz Sinusoidal Wavefomr Ffrom Terminals to Mounting Base for 1 Min.)	2500			Volts

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

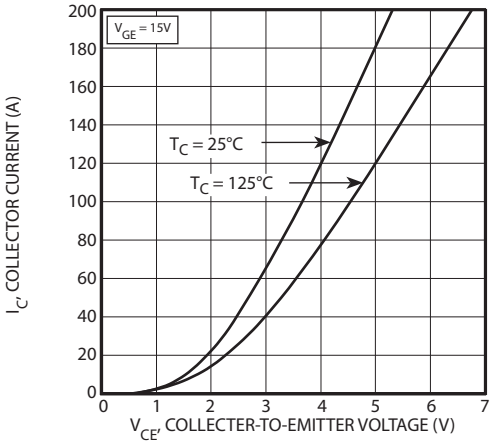


FIGURE 1, Output Characteristics(V_{GE} = 15V)

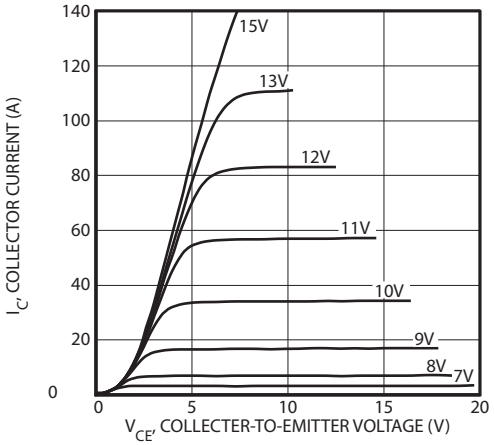


FIGURE 2, Output Characteristics (T_J = 125°C)

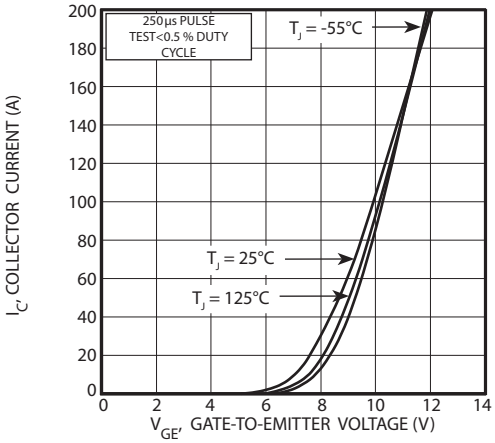


FIGURE 3, Transfer Characteristics

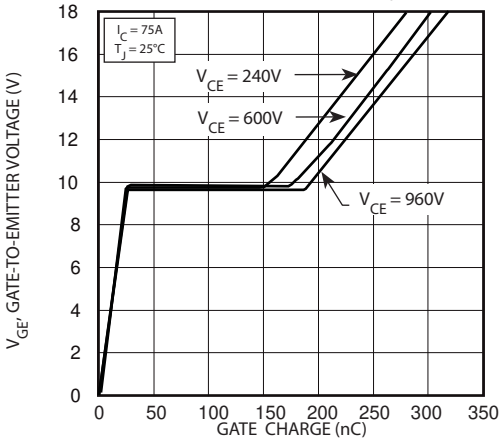


FIGURE 4, Gate Charge

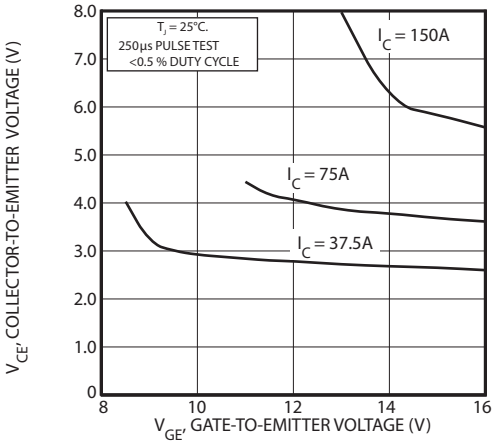


FIGURE 5, On State Voltage vs Gate-to- Emitter Voltage

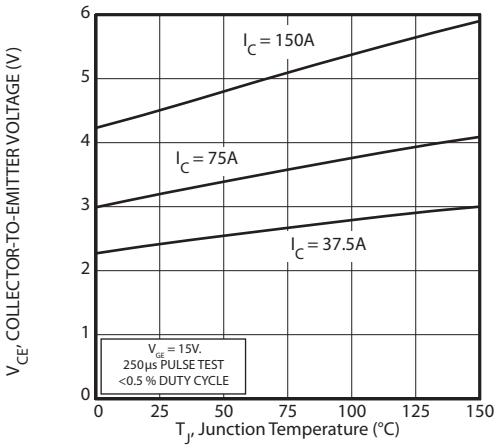


FIGURE 6, On State Voltage vs Junction Temperature

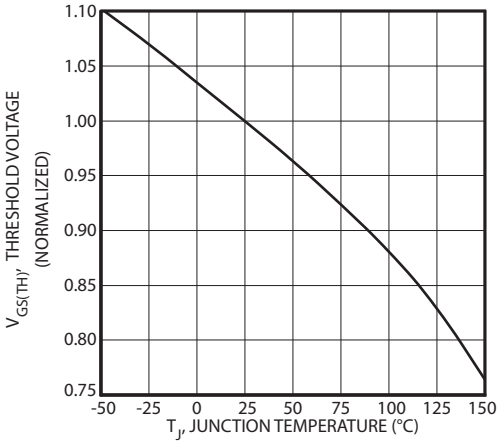


FIGURE 7, Threshold Voltage vs. Junction Temperature

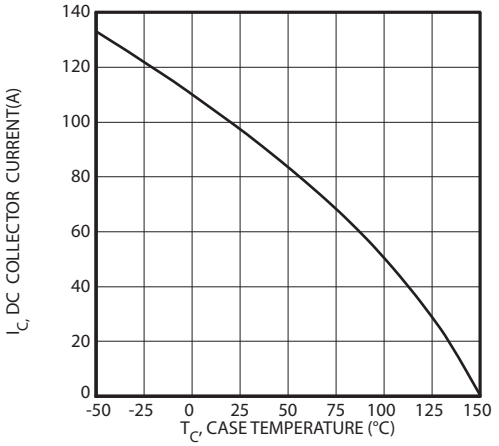


FIGURE 8, DC Collector Current vs Case Temperature

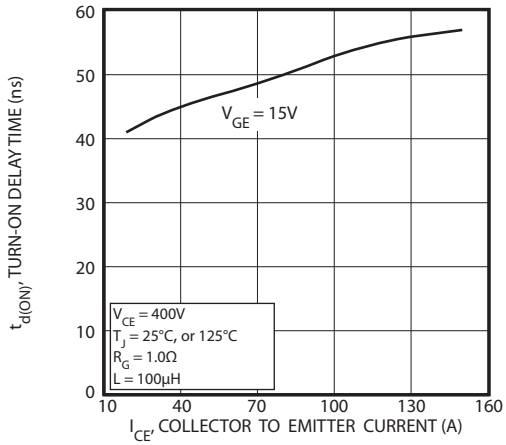


FIGURE 9, Turn-On Delay Time vs Collector Current

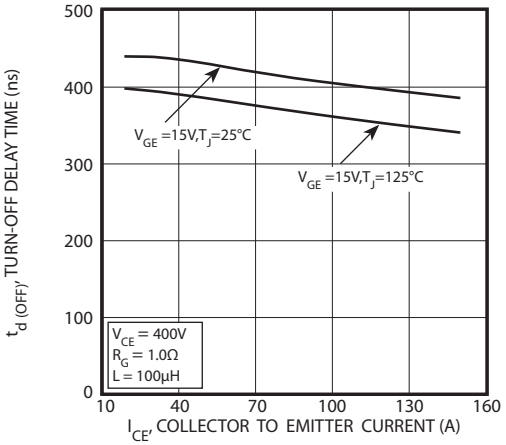


FIGURE 10, Turn-Off Delay Time vs Collector Current

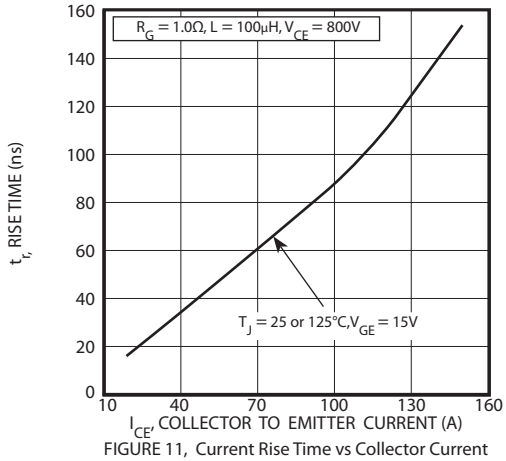


FIGURE 11, Current Rise Time vs Collector Current

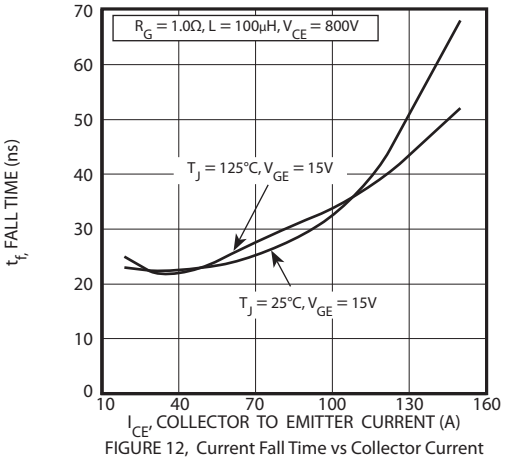


FIGURE 12, Current Fall Time vs Collector Current

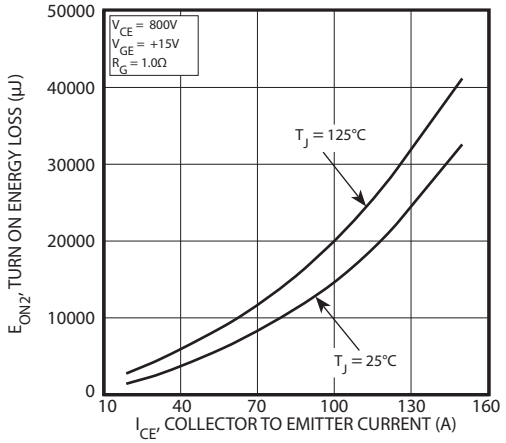


FIGURE 13, Turn-On Energy Loss vs Collector Current

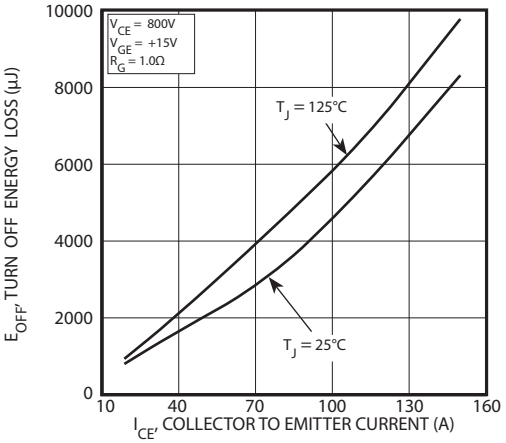


FIGURE 14, Turn Off Energy Loss vs Collector Current

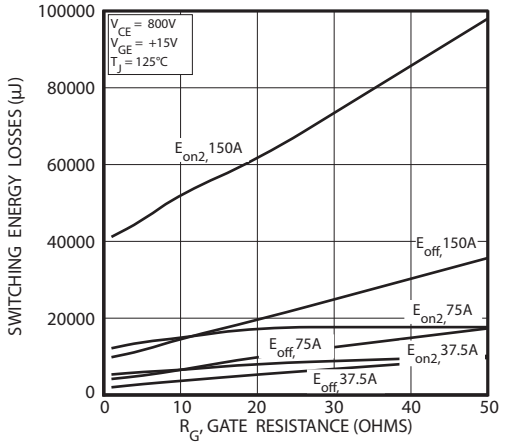


FIGURE 15, Switching Energy Losses vs. Gate Resistance

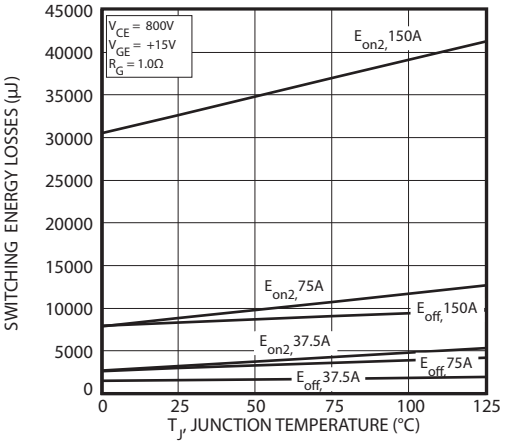


FIGURE 16, Switching Energy Losses vs Junction Temperature

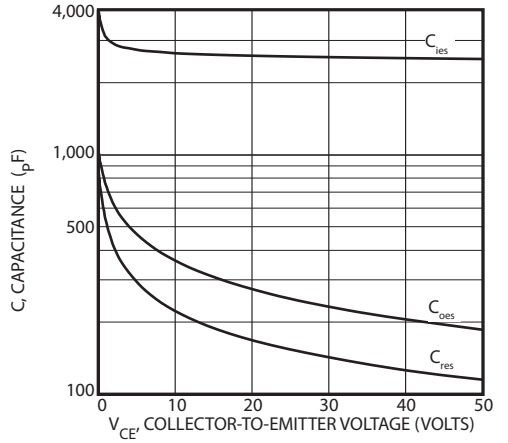


Figure 17, Capacitance vs Collector-To-Emitter Voltage

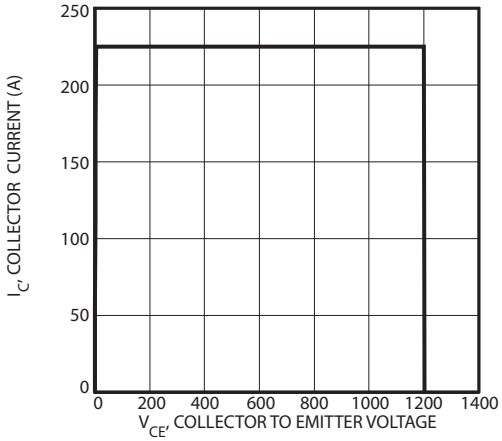


Figure 18,Minimim Switching Safe Operating Area

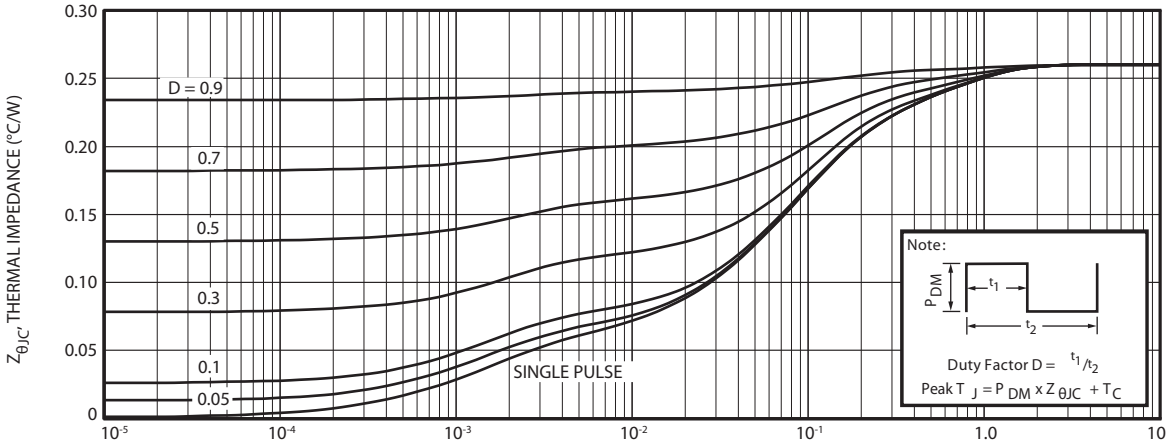


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

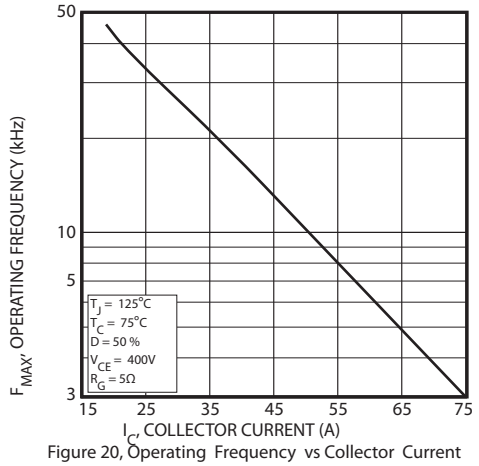


Figure 20, Operating Frequency vs Collector Current

$$F_{max} = \min (f_{max}, f_{max2})$$

$$f_{max1} = \frac{0.05}{t_{d(on)} + t_r + t_{d(off)} + t_f}$$

$$f_{max2} = \frac{P_{diss} - P_{cond}}{E_{on2} + E_{off}}$$

$$P_{diss} = \frac{T_J - T_C}{R_{\theta JC}}$$

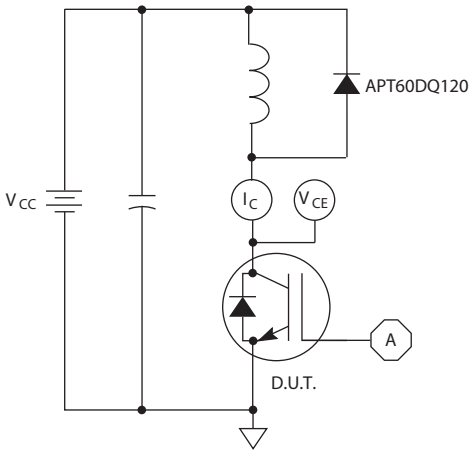


Figure 21, Inductive Switching Test Circui t

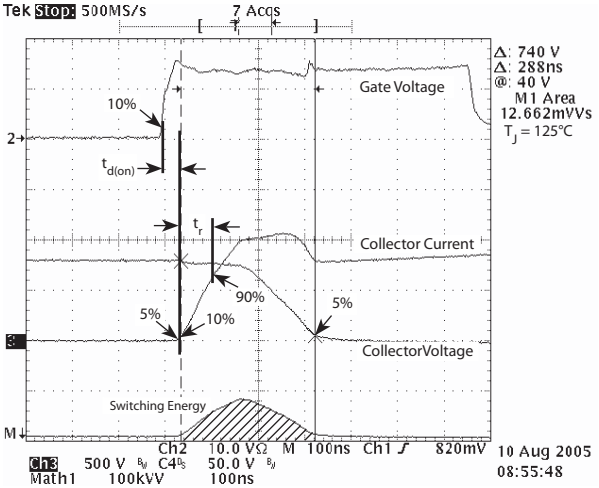


Figure 22, Turn-on Switching Waveforms and Definitions

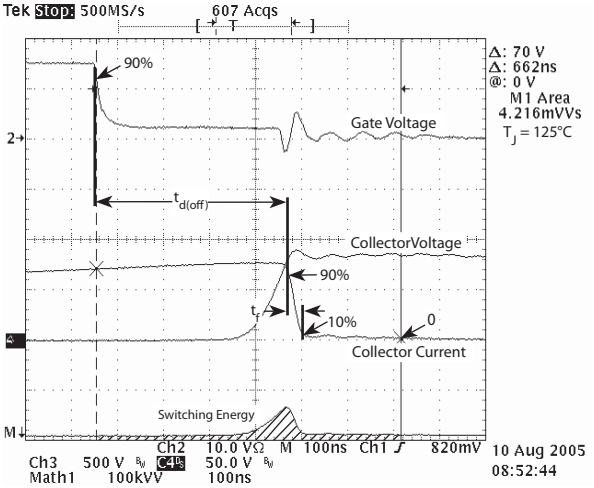


Figure 23, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT75GN120JRDQ3			UNIT
$I_F(AV)$	Maximum Average Forward Current (T_C = 85°C, Duty Cycle = 0.5)		60		Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)		73		
I_{FSM}	Non-Repetitive Forward Surge Current (T_J = 45°C, 8.3ms)		540		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V_F	Forward Voltage	I_F = 75A		2.8		Volts
		I_F = 150A		3.48		
		I_F = 75A, T_J = 125°C		2.17		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX-	UNIT
t_{rr}	Reverse Recovery Time	I_F = 1A, di_F/dt = -100A/µs, V_R = 30V, T_J = 25°C	-	60		ns
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs, V_R = 800V, T_C = 25°C	-	265		ns
Q_{rr}	Reverse Recovery Charge		-	560		nC
I_{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs, V_R = 800V, T_C = 125°C	-	350		ns
Q_{rr}	Reverse Recovery Charge		-	2890		nC
I_{RRM}	Maximum Reverse Recovery Current		-	13	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -1000A/µs, V_R = 800V, T_C = 125°C	-	150		ns
Q_{rr}	Reverse Recovery Charge		-	4720	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	40		Amps

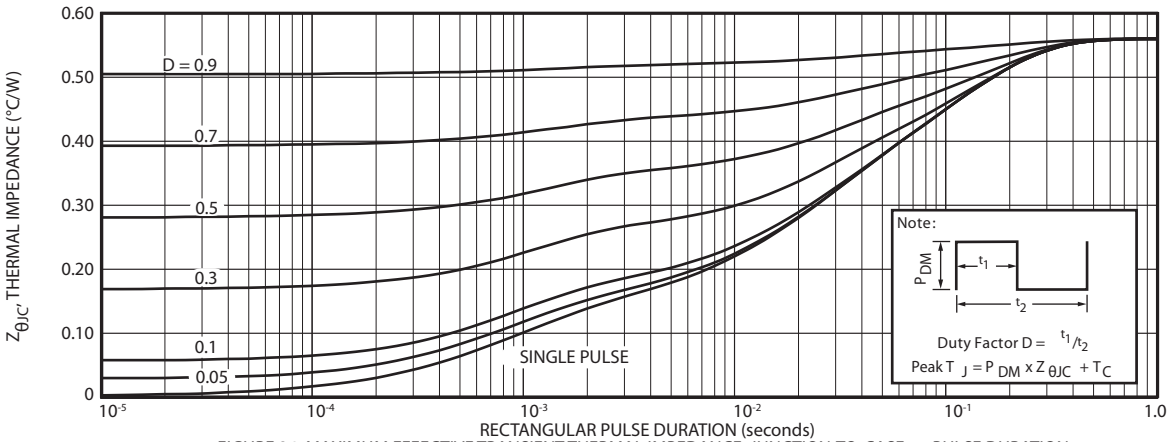


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

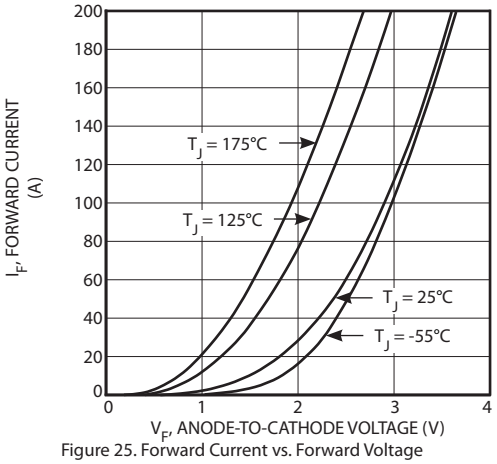


Figure 25. Forward Current vs. Forward Voltage

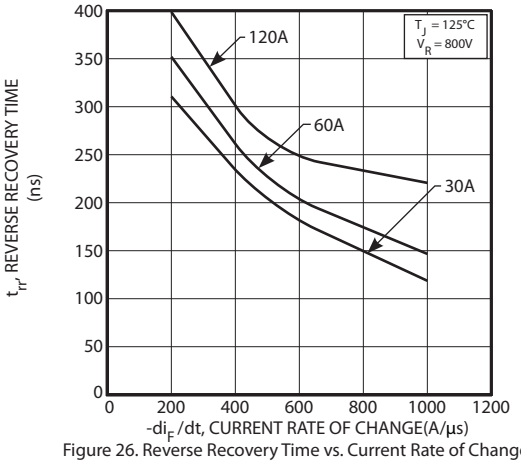


Figure 26. Reverse Recovery Time vs. Current Rate of Change

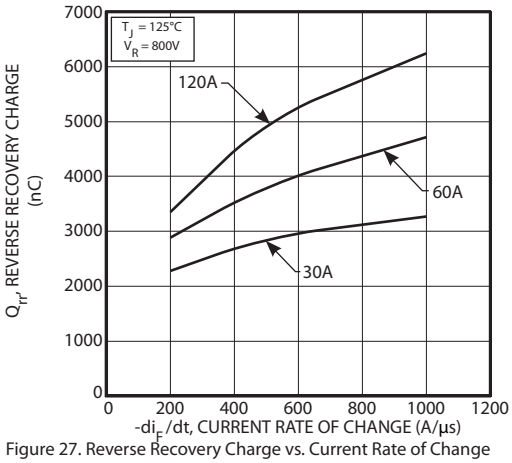


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

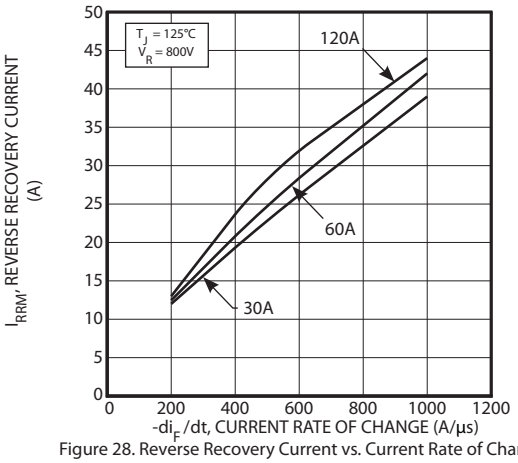


Figure 28. Reverse Recovery Current vs. Current Rate of Change

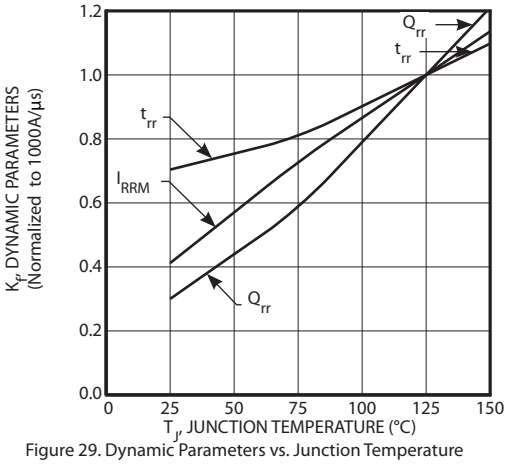


Figure 29. Dynamic Parameters vs. Junction Temperature

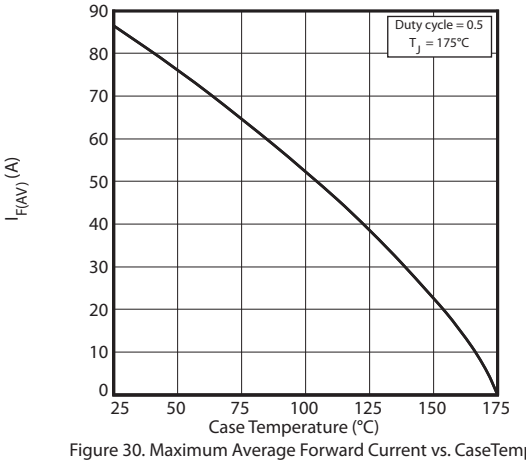


Figure 30. Maximum Average Forward Current vs. CaseTemperature

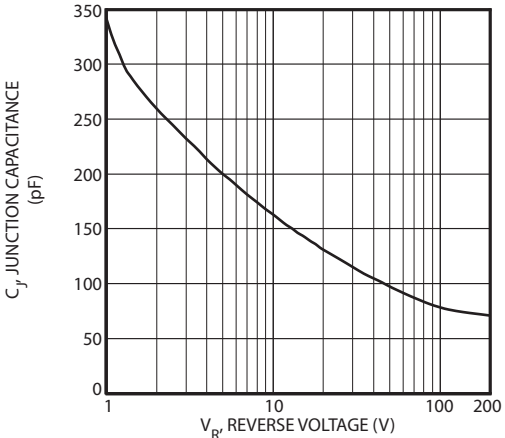


Figure 31. Junction Capacitance vs. Reverse Voltage

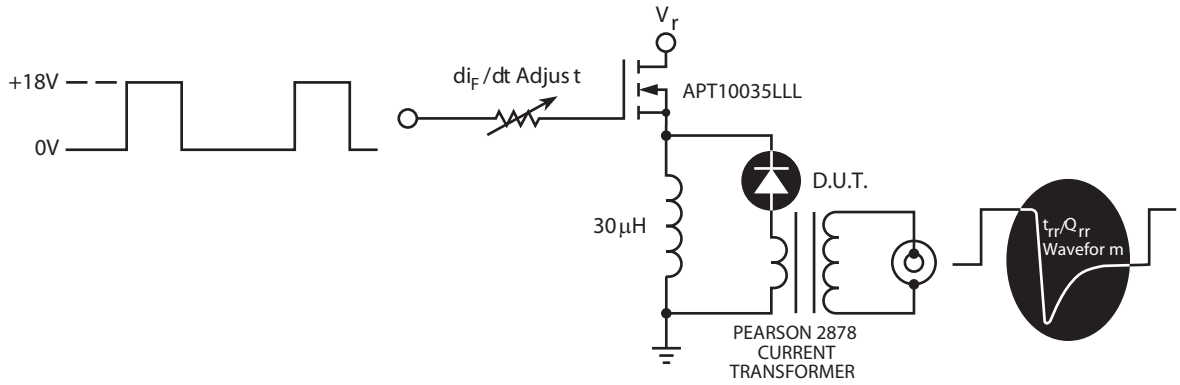
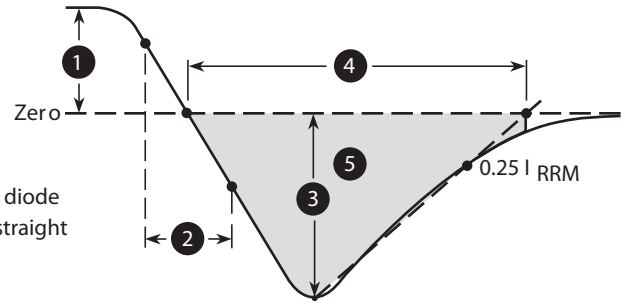


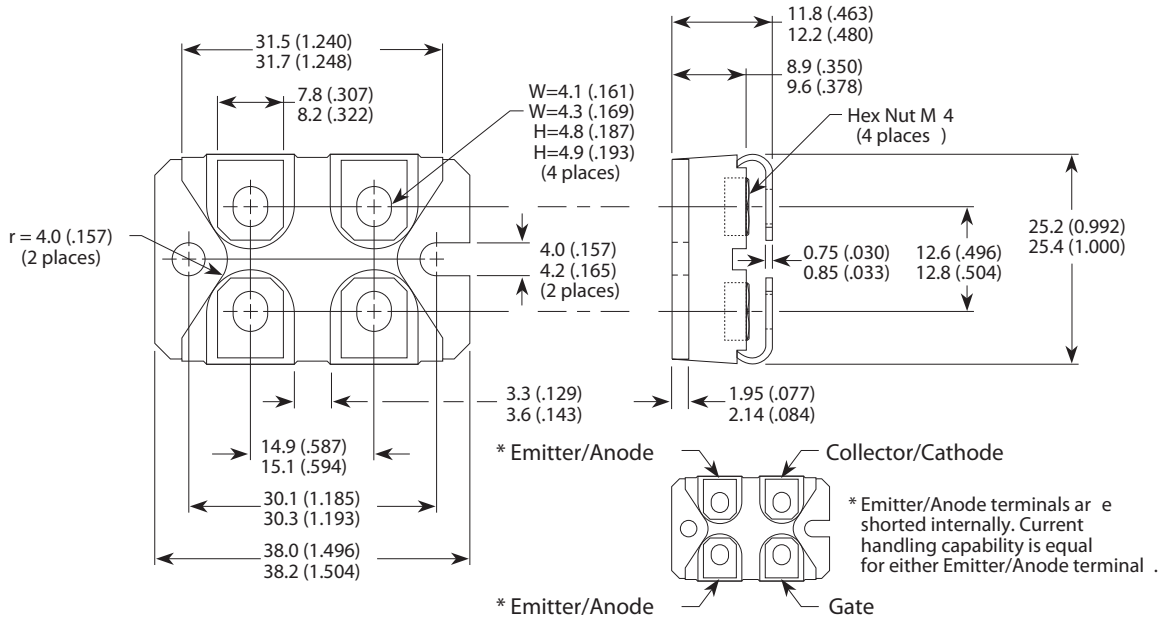
Figure 32. Diode Test Circuit



1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25 I_{RRM} passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

Figure 33, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)